Issai Shlimak

List of Publications by Year
in descending order

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28	202	1163117 8	1125743 13
papers	citations	h-index	g-index

28	28	28	287
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Evidence of structural changes in ion-irradiated graphene independent of the incident ions mass. Applied Surface Science, 2022, 597, 153701.	6.1	3
2	Analysis of fluctuations in the Raman spectra of suspended and supported graphene films. Applied Surface Science, 2021, 536, 147812.	6.1	4
3	Irradiation-induced broadening of the Raman spectra in monolayer graphene. Journal of Applied Physics, 2019, 126, .	2.5	13
4	Effect of annealing on Raman spectra of monolayer graphene samples gradually disordered by ion irradiation. Journal of Applied Physics, 2017, 121, 114301.	2.5	19
5	Charge carrier transport asymmetry in monolayer graphene. Physical Review B, 2017, 96, .	3.2	8
6	Influence of ageing on Raman spectra and the conductivity of monolayer graphene samples irradiated by heavy and light ions. Journal of Applied Physics, 2016, 120, .	2.5	10
7	Fast optoelectronic responsivity of metal-oxide-semiconductor nanostructures. Journal of Nanophotonics, 2016, 10, 036001.	1.0	6
8	Hopping magnetoresistance in ion irradiated monolayer graphene. Physica E: Low-Dimensional Systems and Nanostructures, 2016, 76, 158-163.	2.7	16
9	Raman scattering and electrical resistance of highly disordered graphene. Physical Review B, 2015, 91, .	3.2	29
10	Localization of Charge Carriers in Monolayer Graphene Gradually Disordered by Ion Irradiation. Graphene, 2015, 04, 45-53.	1.0	23
11	Direct observation of a multiple-peak structure in the Raman spectra of 74Ge and 70Ge nanocrystals. Journal of Applied Physics, 2013, 113, .	2.5	0
12	Irradiation of germanium nanocrystals with reactor neutrons. Physics of the Solid State, 2012, 54, 2201-2204.	0.6	0
13	Fabrication of uniform Ge-nanocrystals embedded in amorphous SiO2 films using Ge-ion implantation and neutron irradiation methods. Applied Physics Letters, 2011, 98, .	3.3	8
14	Longitudinal resistivity in the quantum Hall effect regime in a split-gate Si MOSFET with variable electron density. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 839-841.	0.8	1
15	Long-lived spin echoes in a magnetically dilute system: An NMR study of Ge single crystals. Physical Review B, 2007, 76, .	3.2	7
16	Quantum information processing based onP31nuclear spin qubits in a quasi-one-dimensionalSi28nanowire. Physical Review B, 2007, 75, .	3.2	6
17	NMR study of the isotopically engineered Ge single crystals. Hyperfine Interactions, 2007, 180, 1-5.	0.5	0
18	Disorder-induced features of the transverse resistance in a Si-MOSFET in the quantum Hall effect regime. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 309-312.	0.8	4

#	Article	IF	Citations
19	Influence of Neutron Transmutation Doping on Optical Properties of Ge nanocrystals Prepared by Ion implantation. Materials Research Society Symposia Proceedings, 2005, 908, 1.	0.1	0
20	Conductivity of weakly and strongly localized electrons in an-type Si/SiGe heterostructure. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 67-70.	0.8	3
21	Two-dimensional variable-range hopping conductivity: Influence of the electron-ectron interaction. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 2001, 81, 1093-1103.	0.6	6
22	Analysis of the Critical Behavior of the Metal-Insulator Transition by Variation of the Compensation in Neutron Transmutation Doped74Ge-70Ge Crystals. Physica Status Solidi (B): Basic Research, 2000, 218, 233-236.	1.5	4
23	Influence of disorder in compensation-doped germanium on the critical indices of the metal-insulator transition. Physics of the Solid State, 1999, 41, 757-760.	0.6	2
24	The Scaling Behaviour of the Metal-Insulator Transition of Isotopically Engineered Neutron-Transmutation Doped Germanium. Physica Status Solidi (B): Basic Research, 1998, 205, 269-273.	1.5	16
25	New Approach for Determination of the Critical Behavior of Conductivity near the Metal-Insulator Transition in Doped Semiconductors. Physica Status Solidi (B): Basic Research, 1998, 205, 287-293.	1.5	5
26	Role of electron â€œlakesâ€•in the negative magnetoresistance effect in the region of Mott hopping conductivity. JETP Letters, 1996, 63, 199-203.	1.4	5
27	Determination of the impurity concentration in heavily doped inhomogeneous semiconductors from the measurement of the low-temperature conductivity. Applied Physics A: Materials Science and Processing, 1995, 61, 115-118.	2.3	3
28	Determination of the impurity concentration in heavily doped inhomogeneous semiconductors from the measurement of the low-temperature conductivity. Applied Physics A: Materials Science and Processing, 1995, 61, 115-118.	2.3	1